

N-channel 650 V, 0.215 Ω typ., 12.5 A MDmesh™ V Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - production data

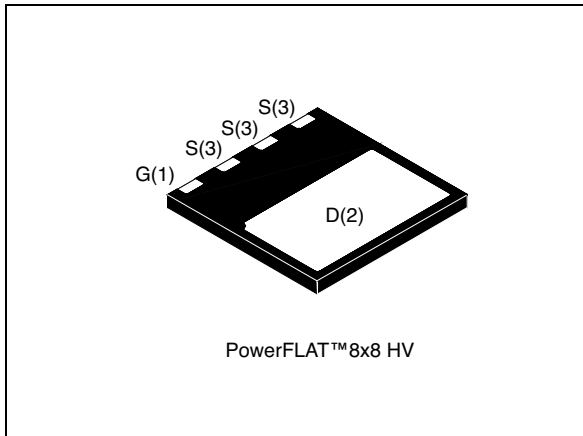
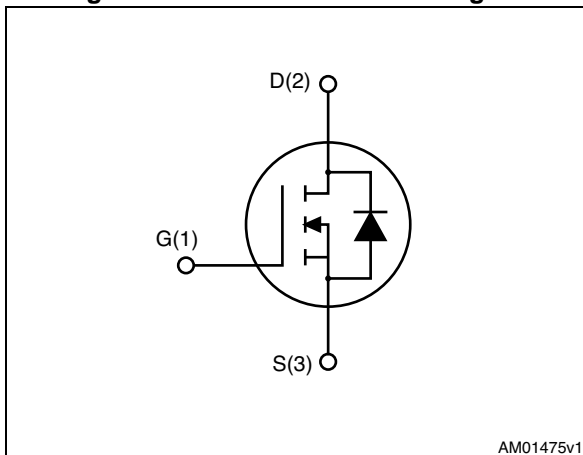


Figure 1. Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)max.}	I _D
STL19N65M5	710 V	0.240 Ω	12.5 A ⁽¹⁾

1. The value is rated according to R_{thj-case} and limited by package.

- Worldwide best R_{DS(on)} * area
- Higher V_{DSS} rating and high dv/dt capability
- Excellent switching performance

Applications

- Switching applications

Description

This device is an N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL19N65M5	19N65M5	PowerFLAT™ 8x8 HV	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
5	Packaging mechanical data	14
6	Revision history	16



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	12.5	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	8.3	A
$I_{DM}^{(1),(2)}$	Drain current (pulsed)	50	A
$I_D^{(3)}$	Drain current (continuous) at $T_{amb} = 25\text{ }^\circ\text{C}$	2.3	A
$I_D^{(3)}$	Drain current (continuous) at $T_{amb} = 100\text{ }^\circ\text{C}$	1.5	A
$P_{TOT}^{(3)}$	Total dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	2.8	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	4	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	210	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area.
3. When mounted on FR-4 board of inch^2 , 2oz Cu
4. $I_{SD} \leq 12.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{Peak} \leq V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.39	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb max	45	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$		0.215	0.240	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	1240	-	pF
C_{oss}	Output capacitance		-	32	-	pF
C_{rss}	Reverse transfer capacitance		-	3	-	pF
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0,$ $V_{DS} = 0\text{ to }80\% V_{(BR)DSS}$	-	30	-	pF
$C_{o(tr)}^{(2)}$	Equivalent capacitance time related		-	99	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	3	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 7.5\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 16)	-	31	-	nC
Q_{gs}	Gate-source charge		-	8	-	nC
Q_{gd}	Gate-drain charge		-	14	-	nC

- $C_{oss\text{ eq}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
- $C_{oss\text{ eq}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 9.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17 and 20)	-	36	-	ns
$t_{r(v)}$	Voltage rise time		-	7	-	ns
$t_{f(i)}$	Current fall time		-	9	-	ns
$t_{c(off)}$	Crossing time		-	11	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		12.5	A
$I_{SDM}^{(1),(2)}$	Source-drain current (pulsed)		-		50	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD} = 15\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 17)	-	290		ns
Q_{rr}	Reverse recovery charge		-	3.4		μC
I_{RRM}	Reverse recovery current		-	23.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	352		ns
Q_{rr}	Reverse recovery charge		-	4		μC
I_{RRM}	Reverse recovery current		-	24		A

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area
3. Pulsed: pulse duration = $300\ \mu\text{s}$, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

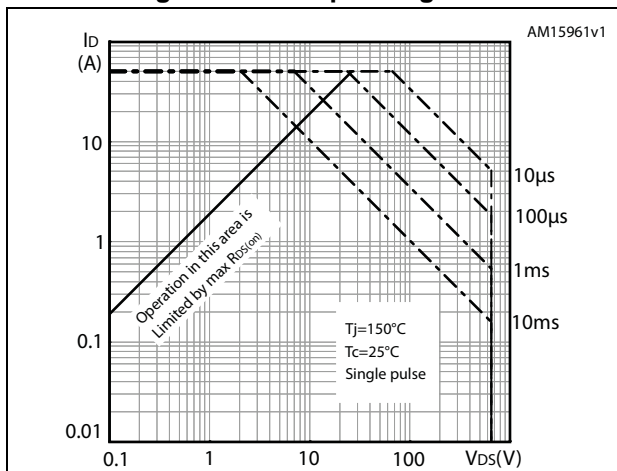


Figure 3. Thermal impedance

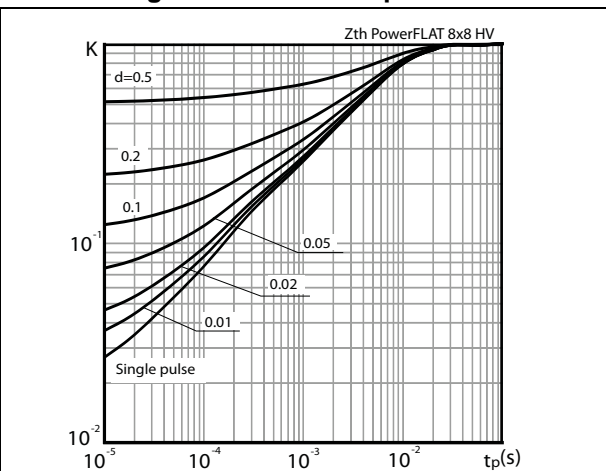


Figure 4. Output characteristics

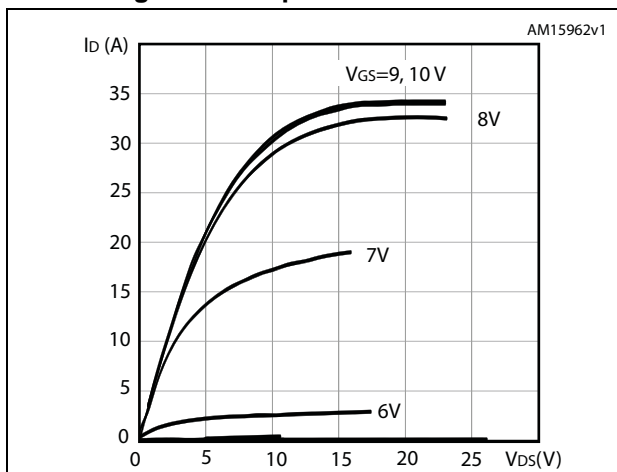


Figure 5. Transfer characteristics

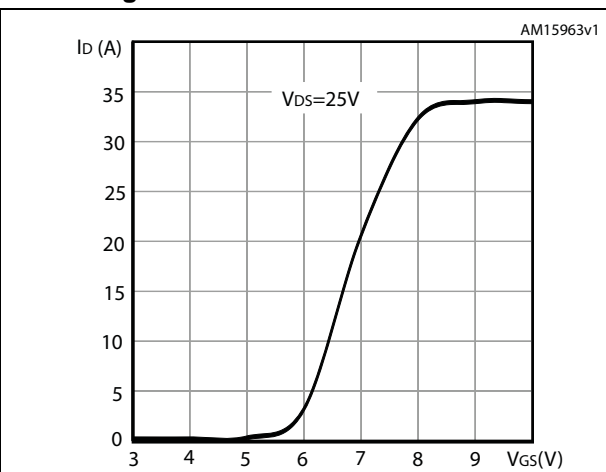


Figure 6. Gate charge vs gate-source voltage

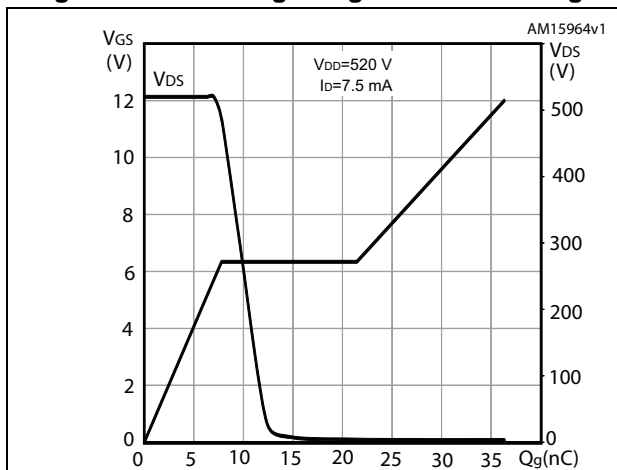


Figure 7. Static drain-source on-resistance

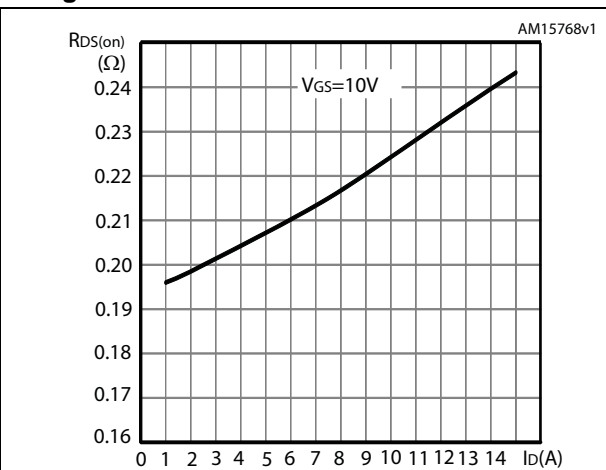


Figure 8. Capacitance variations

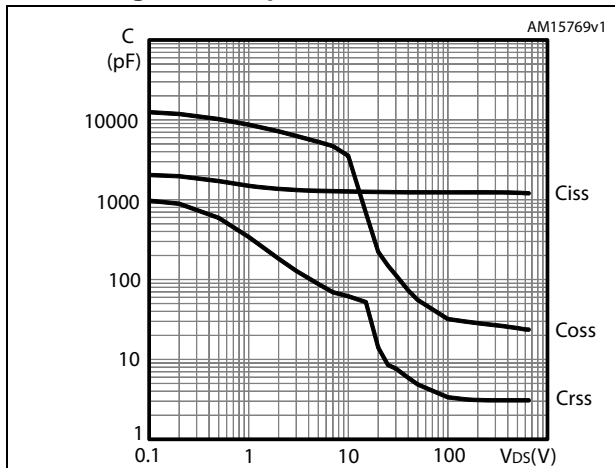


Figure 9. Output capacitance stored energy

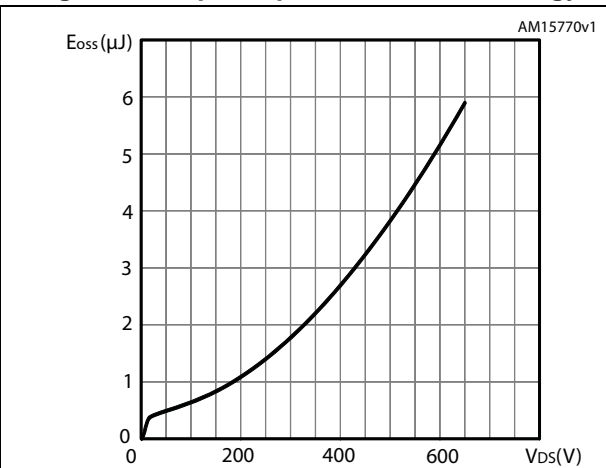


Figure 10. Normalized gate threshold voltage vs. temperature

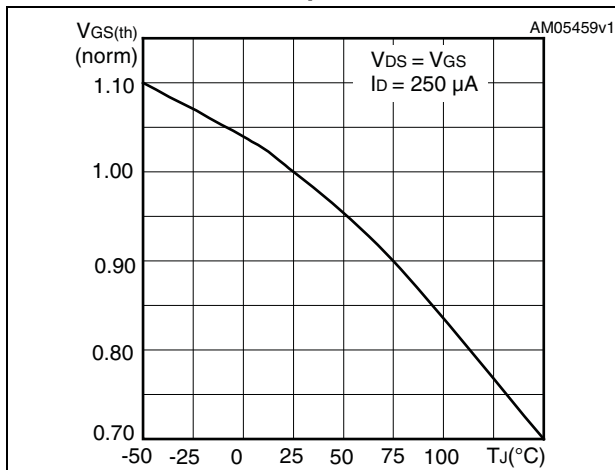


Figure 11. Normalized on-resistance vs. temperature

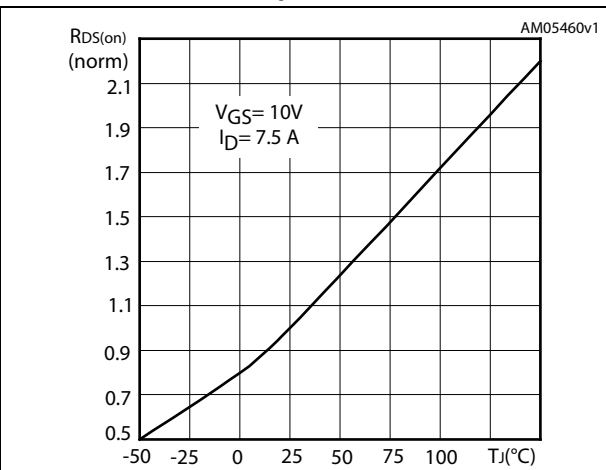


Figure 12. Drain-source diode forward characteristics

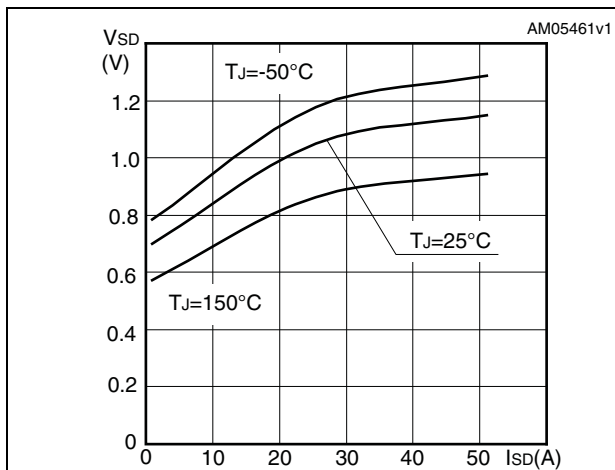


Figure 13. Normalized VDS vs. temperature

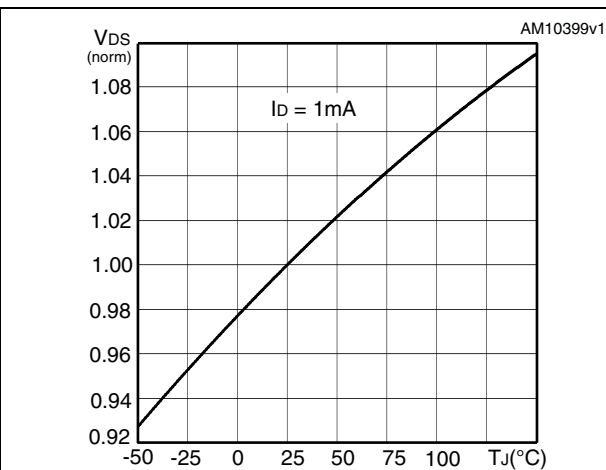
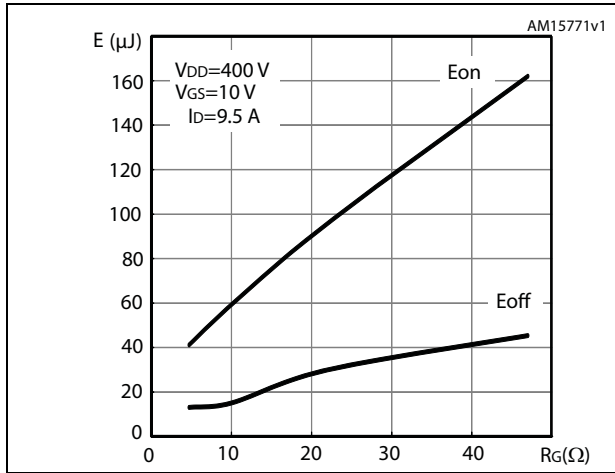


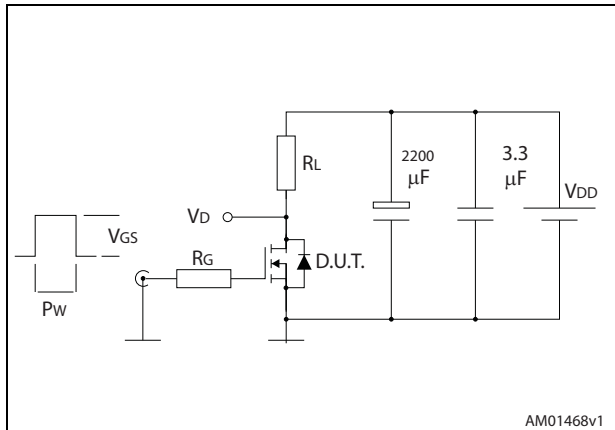
Figure 14. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

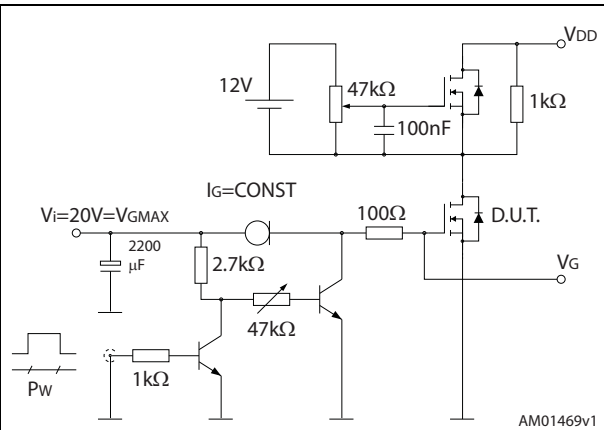
3 Test circuits

Figure 15. Switching times test circuit for resistive load



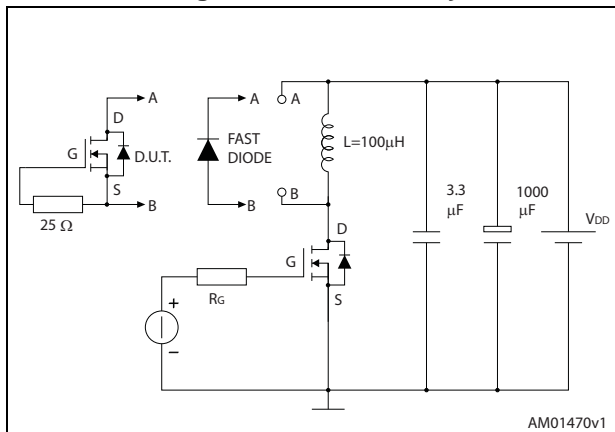
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Figure 16. Gate charge test circuit



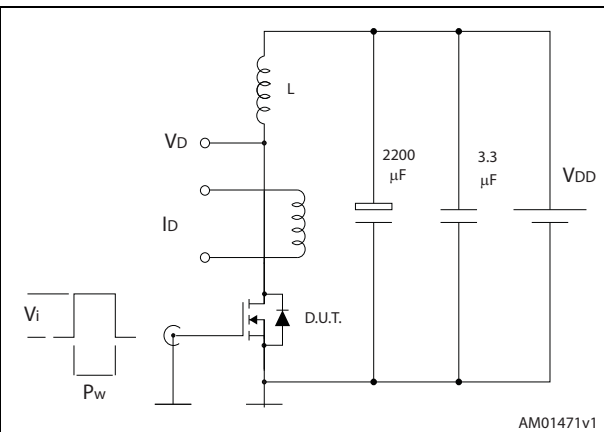
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Figure 17. Test circuit for inductive load switching and diode recovery times



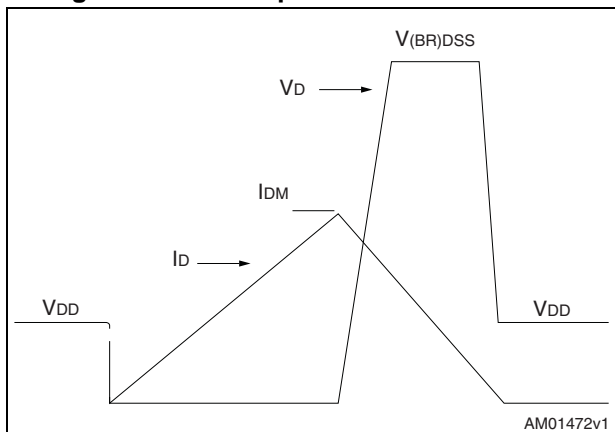
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Figure 18. Unclamped inductive load test circuit



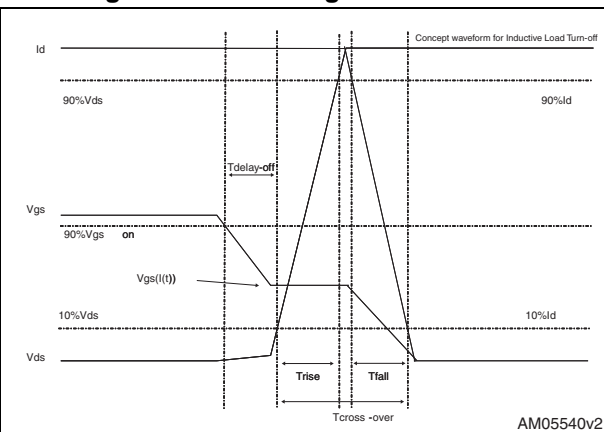
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Figure 19. Unclamped inductive waveform



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Figure 20. Switching time waveform



AM05540v2

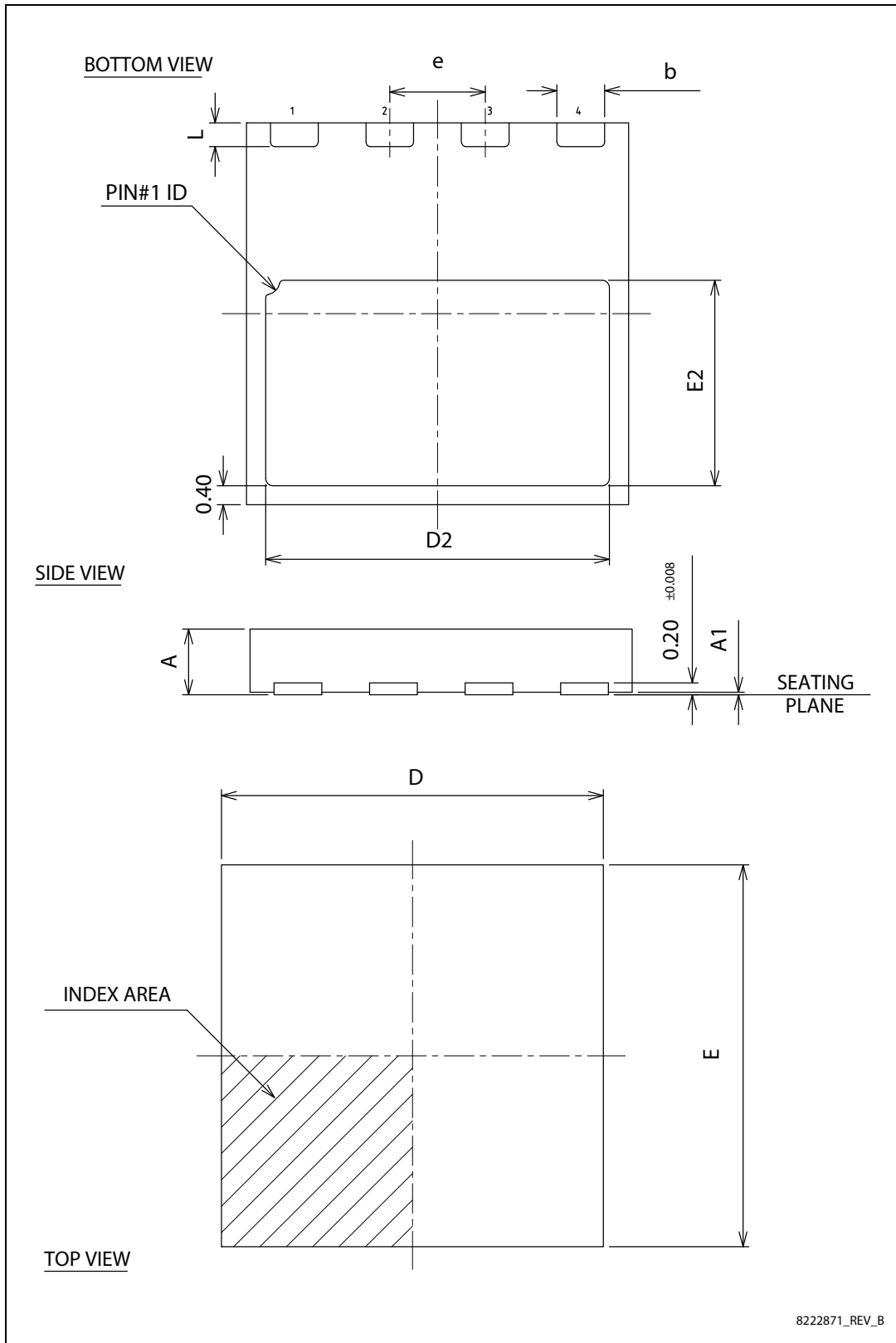
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. PowerFLAT™ 8x8 HV mechanical data

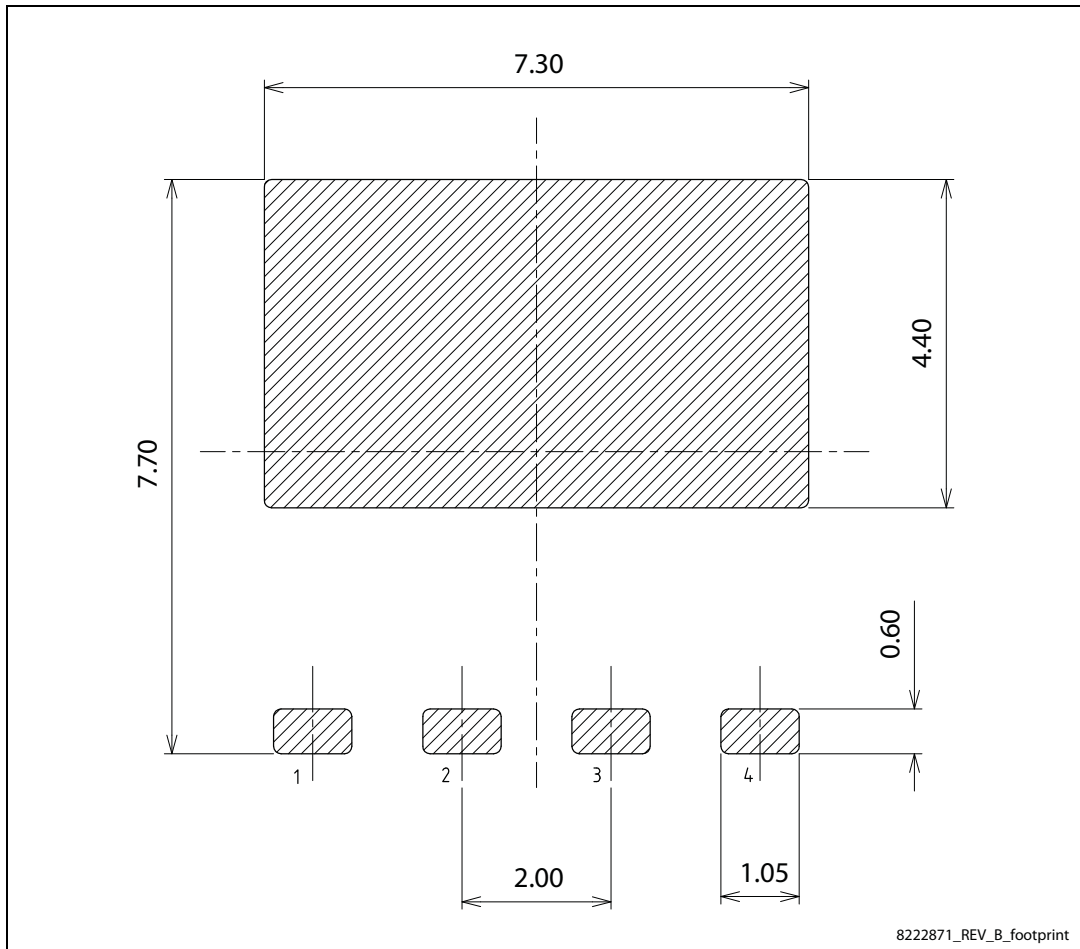
Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60

Figure 21. PowerFLAT™ 8x8 HV drawing mechanical data



8222871_REV_B

Figure 22. PowerFLAT™ 8x8 HV recommended footprint (dimension in millimeters)



5 Packaging mechanical data

Figure 23. PowerFLAT™ 8x8 HV tape (dimension in millimeters)

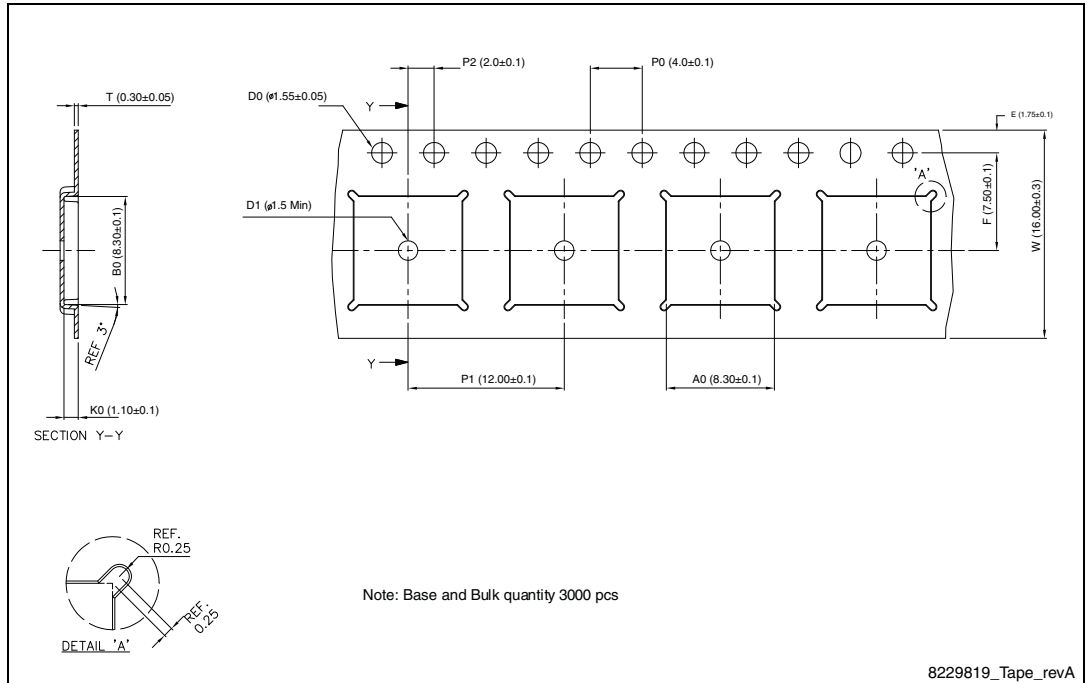


Figure 24. PowerFLAT™ 8x8 HV package orientation in carrier tape

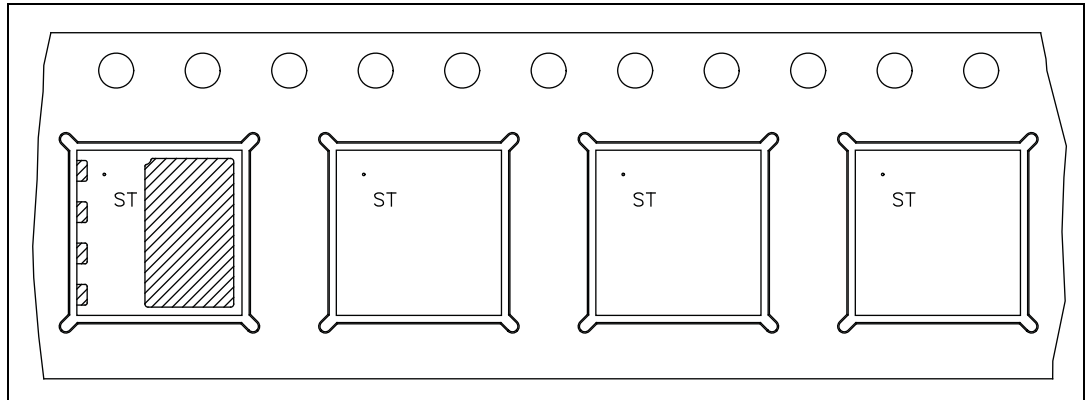
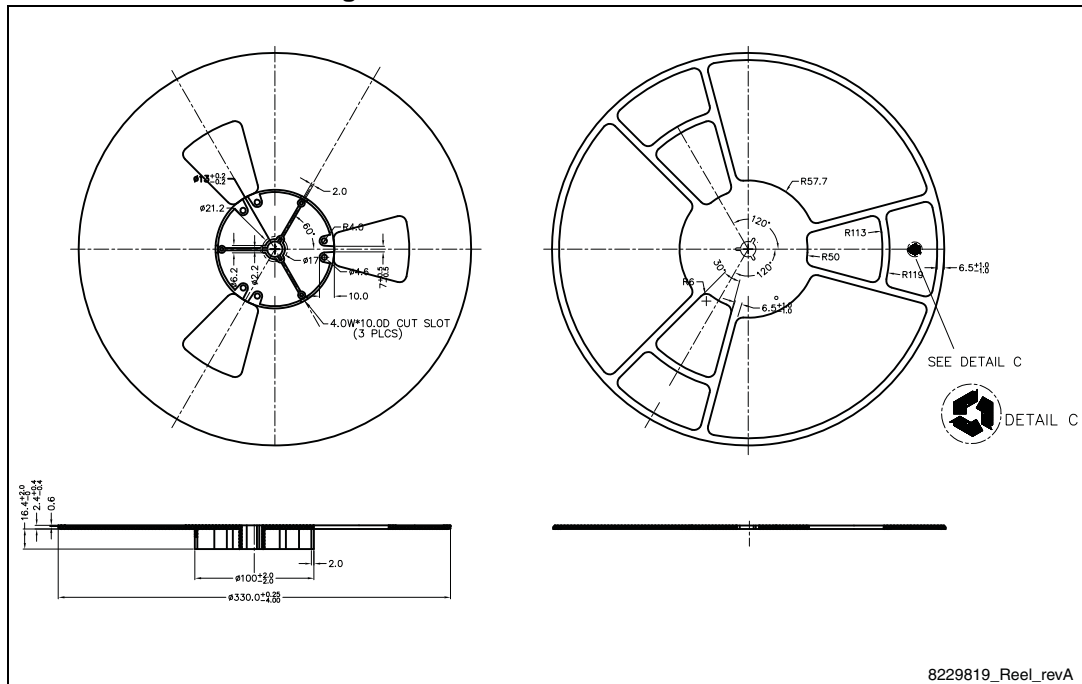


Figure 25. PowerFLAT™ 8x8 HV reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
17-Jul-2013	1	First release

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